

Silicon PNP Power Transistors

2SA1726

DESCRIPTION

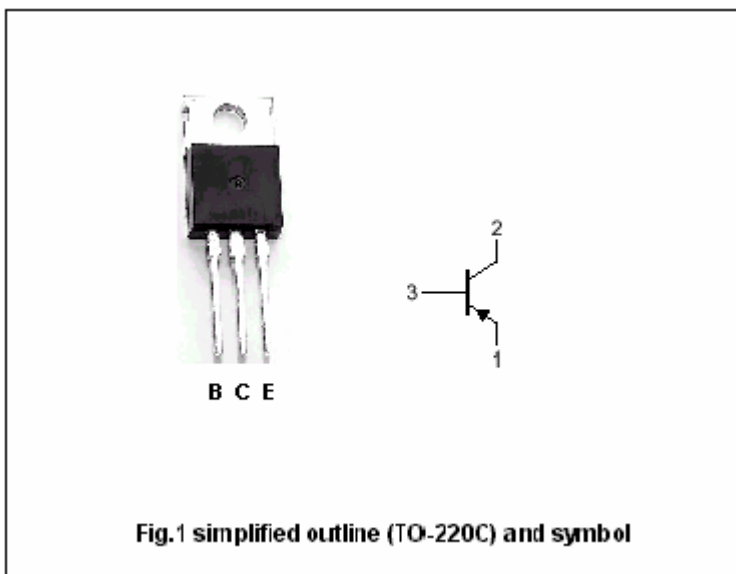
- With TO-220C package
- Complement to type 2SC4512

APPLICATIONS

- Audio and General Purpose

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-80	V
V _{CEO}	Collector-emitter voltage	Open base	-80	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-6	A
I _B	Base current		-3	A
P _C	Collector dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA; R _{BE} =	-80			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-2A; I _B =-0.2A			-0.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-80V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-10	μA
h _{FE}	DC current gain	I _C =-2A; V _{CE} =-4V	50			
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =-10V		150		pF
f _T	Transition frequency	I _E =0.5A; V _{CE} =-12V		20		MHz

Switching times

t _{on}	Turn-on time	V _{CC} =-30V; I _C =-3A I _{B1} =-I _{B2} =-0.3A R _L =10		0.18		μs
t _{stg}	Storage time			1.10		μs
t _f	Fall time			0.21		μs

◆ h_{FE} Classifications

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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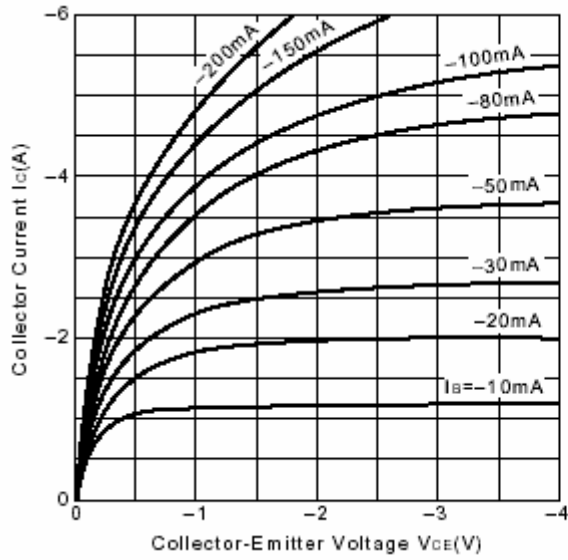


Fig.3 Static Characteristic

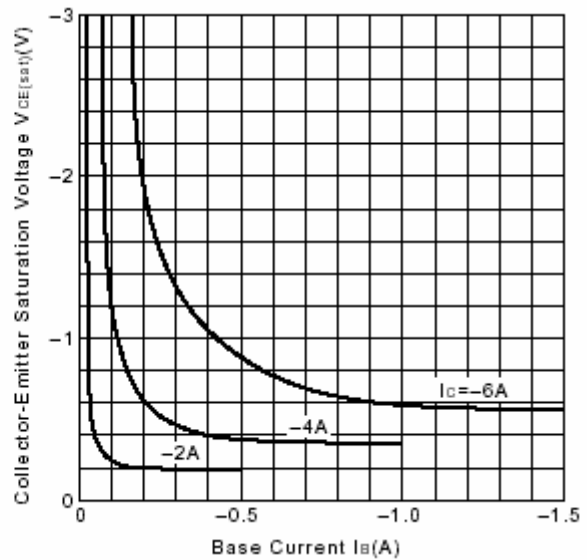


Fig.4 $V_{CE(sat)}-I_B$ Characteristics

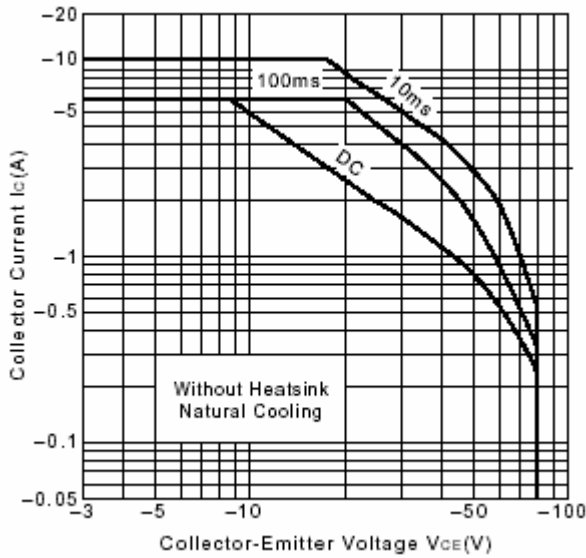


Fig.5 Safe Operating Area

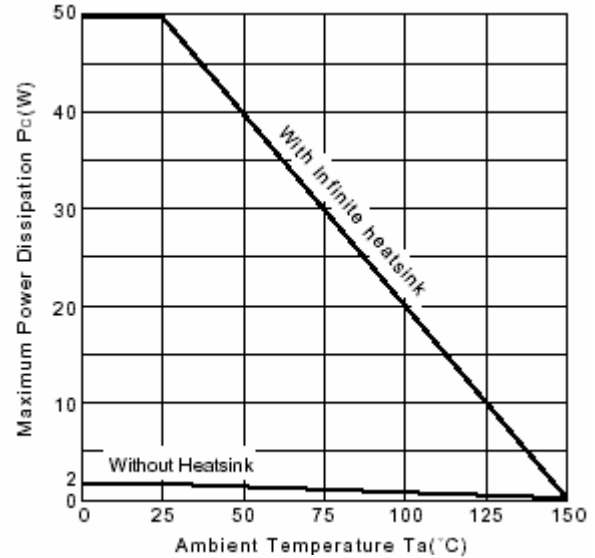


Fig.6 P_c-T_a Derating

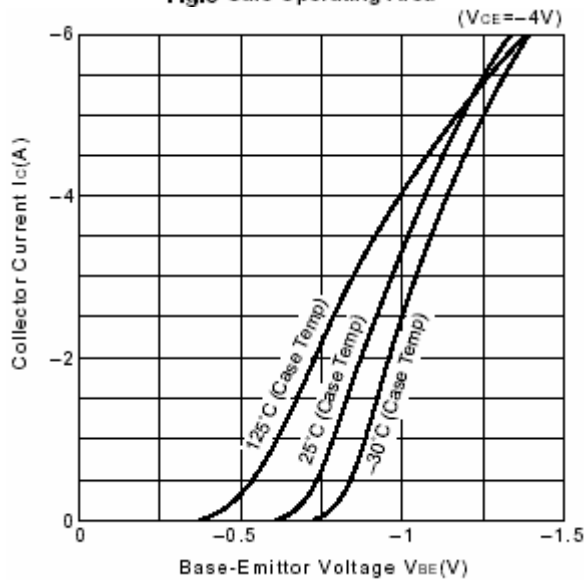


Fig.7 I_C-V_{BE}

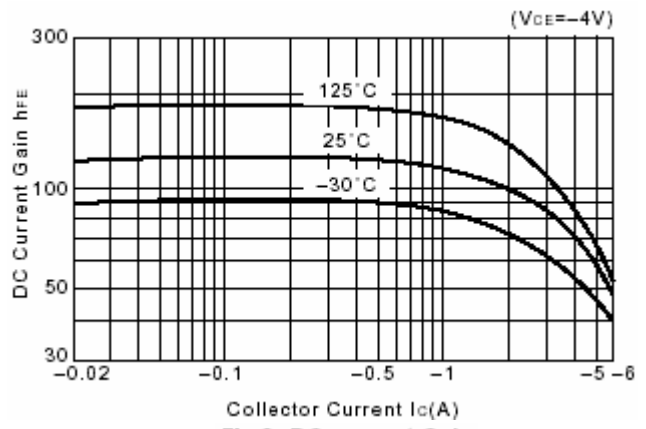


Fig.8 DC current Gain